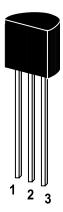


NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	25	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ic	700	mA
Power Dissipation	P _{tot}	600	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°C









Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =1V, I _C =100mA					
Current Gain Group O	h _{FE}	90	-	180	-
Y	h _{FE}	135	-	270	-
G	h _{FE}	200	-	400	-
at V _{CE} =1V, I _C =700mA	h _{FE}	50	-	-	-
Collector Base Breakdown Voltage					
at I _C =10μA	$V_{(BR)CBO}$	30	-	-	V
Base Emitter Voltage					
at I _C =10mA, V _{CE} =6V	V_{BE}	0.6	-	0.7	V
Emitter Cutoff Current					
at V _{EB} =5V	I _{EBO}	-	-	0.1	μΑ
Collector Cutoff Current					
at V _{CB} =30V	I _{CBO}	-	-	0.1	μΑ
Collector Saturation Voltage					
at I _C =700mA, I _B =70mA	$V_{CE(sat)}$	-	0.2	0.6	V
Base Saturation Voltage					
at I _C =700mA, I _B =70mA	$V_{BE(sat)}$		0.95	1.2	V
Gain Bandwidth Product					
at V _{CE} =6V, I _C =10mA	f_T	50	170	-	MHz
Output Capacitance					
at V _{CB} =6V, f=1MHz	СОВ		13	25	pF







